

WEST Search History

DATE: Friday, March 19, 2004

Hide?	Set Name	Query	Hit Count
<i>DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<input type="checkbox"/>	L36	l34 and l11	57
<input type="checkbox"/>	L35	l34 and l11	57
<input type="checkbox"/>	L34	channel adj7 oxide	15617
<input type="checkbox"/>	L33	cahnnel adj4 oxide	0
<input type="checkbox"/>	L32	cahnnel adj4 oxide	0
<input type="checkbox"/>	L31	5216262	22
<i>DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<input type="checkbox"/>	L30	5216262	22
<input type="checkbox"/>	L29	6472685	3
<i>DB=EPAB; PLUR=YES; OP=OR</i>			
<input type="checkbox"/>	L28	2347520	1
<i>DB=DWPI; PLUR=YES; OP=OR</i>			
<input type="checkbox"/>	L27	L26 and l25	2
<input type="checkbox"/>	L26	tsu.inv.	80
<input type="checkbox"/>	L25	L24 and l23	63
<input type="checkbox"/>	L24	barrier and silicon	5445
<input type="checkbox"/>	L23	wang.inv.	40396
<input type="checkbox"/>	L22	02103767	0
<input type="checkbox"/>	L21	02/103767	0
<i>DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<input type="checkbox"/>	L20	l1 and l19	8
<input type="checkbox"/>	L19	l11 adj20 l18	655
<input type="checkbox"/>	L18	oxide or nitride o fluorine or carbon or carbide	6180325
<input type="checkbox"/>	L17	6699771	1
<input type="checkbox"/>	L16	l2 and l14 and l15	16
<input type="checkbox"/>	L15	oxygen or o?sub.\$	811012
<input type="checkbox"/>	L14	silicon or si	1786914
<input type="checkbox"/>	L13	l7 and l5	56
<input type="checkbox"/>	L12	l11 and l18	0
<input type="checkbox"/>	L11	superlattice	7764
<input type="checkbox"/>	L10	l2 and l8	0

<input type="checkbox"/>	L9	band-modif\$5	0
<input type="checkbox"/>	L8	band adj modif\$5	262
<input type="checkbox"/>	L7	band adj modif\$5 or band-modi\$4	262
<input type="checkbox"/>	L6	l2 and l5	36
<input type="checkbox"/>	L5	monolayer mono\$5 or atom\$5	1483361
<input type="checkbox"/>	L4	L3 and l2	27
<input type="checkbox"/>	L3	parallel	2304355
<input type="checkbox"/>	L2	superlattice adj6 channel	104
<input type="checkbox"/>	L1	superlattice adj6 channel	104

END OF SEARCH HISTORY

Refine Search

Search Results -

Terms	Documents
L18 and L17	2

Database:

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search:

Search History

DATE: Friday, March 19, 2004 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=DWPI; PLUR=YES; OP=OR</i>			
<u>L19</u>	L18 and l17	2	<u>L19</u>
<u>L18</u>	lofgren.inv.	172	<u>L18</u>
<u>L17</u>	L16 and l15	20	<u>L17</u>
<u>L16</u>	wang.inv.	40396	<u>L16</u>
<u>L15</u>	tsu.inv.	80	<u>L15</u>
<u>L14</u>	2103767	7	<u>L14</u>
<u>L13</u>	02103767	0	<u>L13</u>
<i>DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<u>L12</u>	l1 near20 l2	5	<u>L12</u>
<u>L11</u>	L10 near10 l1	34	<u>L11</u>
<u>L10</u>	tilt	166799	<u>L10</u>
<u>L9</u>	l1 and l8	4	<u>L9</u>
<u>L8</u>	5679152	55	<u>L8</u>
<u>L7</u>	l3 and l6	154	<u>L7</u>

WEST Search History

DATE: Friday, March 19, 2004

<u>Hide?</u>	<u>Set Name</u>	<u>Query</u>	<u>Hit Count</u>
	<i>DB=PGPB,USPT,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>		
<input type="checkbox"/>	L20	l1 and l19	8
<input type="checkbox"/>	L19	l11 adj20 l18	655
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<input type="checkbox"/>	L12	l11 and l18	0
<input type="checkbox"/>	L11	superlattice	7764
<input type="checkbox"/>	L10	l2 and l8	0
<input type="checkbox"/>	L9	band-modif\$5	0
<input type="checkbox"/>	L8	band adj modif\$5	262
<input type="checkbox"/>	L7	band adj modif\$5 or band-modi\$4	262
<input type="checkbox"/>	L6	l2 and l5	36
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<input type="checkbox"/>	L4	L3 and l2	27
<input type="checkbox"/>	L3	parallel	2304355
<input type="checkbox"/>	L2	superlattice adj6 channel	104
<input type="checkbox"/>	L1	superlattice adj6 channel	104

END OF SEARCH HISTORY

Hit List

[Clear](#) [Generate Collection](#) [Print](#) [Fwd Refs](#) [Bkwd Refs](#)
[Generate OACS](#)

Search Results - Record(s) 1 through 16 of 16 returned.

☐ 1. Document ID: US 6559469 B1

Using default format because multiple data bases are involved.

L16: Entry 1 of 16

File: USPT

May 6, 2003

US-PAT-NO: 6559469

DOCUMENT-IDENTIFIER: US 6559469 B1

TITLE: Ferroelectric and high dielectric constant transistors

DATE-ISSUED: May 6, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Paz de Araujo; Carlos A.	Colorado Springs	CO		
McMillan; Larry D.	Colorado Springs	CO		
Joshi; Vikram	Colorado Springs	CO		
Solayappan; Narayan	Colorado Springs	CO		
Cuchiario; Joseph D.	Colorado Springs	CO		

US-CL-CURRENT: [257/15](#), [257/16](#), [257/17](#), [257/18](#), [257/19](#), [257/20](#), [257/21](#), [257/22](#),
[257/295](#), [257/E21.011](#), [257/E21.272](#), [257/E27.085](#), [257/E27.104](#)

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KVMC	Draw D
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☐ 2. Document ID: US 6426536 B1

L16: Entry 2 of 16

File: USPT

Jul 30, 2002

US-PAT-NO: 6426536

DOCUMENT-IDENTIFIER: US 6426536 B1

TITLE: Double layer perovskite oxide electrodes

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KVMC	Draw D
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☐ 3. Document ID: US 6355951 B1

L16: Entry 3 of 16

File: USPT

Mar 12, 2002

US-PAT-NO: 6355951

DOCUMENT-IDENTIFIER: US 6355951 B1

TITLE: Field effect semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KM/C	Draw D
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☐ 4. Document ID: US 6294446 B1

L16: Entry 4 of 16

File: USPT

Sep 25, 2001

US-PAT-NO: 6294446

DOCUMENT-IDENTIFIER: US 6294446 B1

TITLE: Methods of manufacturing a high electron mobility transistor with a T-shaped gate electrode

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KM/C	Draw D
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☐ 5. Document ID: US 5952672 A

L16: Entry 5 of 16

File: USPT

Sep 14, 1999

US-PAT-NO: 5952672

DOCUMENT-IDENTIFIER: US 5952672 A

TITLE: Semiconductor device and method for fabricating the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KM/C	Draw D
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☐ 6. Document ID: US 5760418 A

L16: Entry 6 of 16

File: USPT

Jun 2, 1998

US-PAT-NO: 5760418

DOCUMENT-IDENTIFIER: US 5760418 A

TITLE: GaAs power semiconductor device operating at a low voltage and method for fabricating the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KM/C	Draw D
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☐ 7. Document ID: US 5639677 A

L16: Entry 7 of 16

File: USPT

Jun 17, 1997

US-PAT-NO: 5639677

DOCUMENT-IDENTIFIER: US 5639677 A

TITLE: Method of making a gaAs power semiconductor device operating at a low

voltage

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw D
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☐ 8. Document ID: US 5432356 A

L16: Entry 8 of 16

File: USPT

Jul 11, 1995

US-PAT-NO: 5432356

DOCUMENT-IDENTIFIER: US 5432356 A

TITLE: Semiconductor heterojunction floating layer memory device and method for storing information in the same

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw D
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☐ 9. Document ID: US 5430310 A

L16: Entry 9 of 16

File: USPT

Jul 4, 1995

US-PAT-NO: 5430310

DOCUMENT-IDENTIFIER: US 5430310 A

TITLE: Field effect transistor

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw D
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☐ 10. Document ID: US 5155053 A

L16: Entry 10 of 16

File: USPT

Oct 13, 1992

US-PAT-NO: 5155053

DOCUMENT-IDENTIFIER: US 5155053 A

TITLE: Method of forming T-gate structure on microelectronic device substrate

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw D
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☐ 11. Document ID: US 5055887 A

L16: Entry 11 of 16

File: USPT

Oct 8, 1991

US-PAT-NO: 5055887

DOCUMENT-IDENTIFIER: US 5055887 A

TITLE: FET with a super lattice channel

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC	Draw D
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☐ 12. Document ID: US 5021839 A

L16: Entry 12 of 16

File: USPT

Jun 4, 1991

US-PAT-NO: 5021839

DOCUMENT-IDENTIFIER: US 5021839 A

TITLE: FET with a super lattice channel

Full	Title	Citation	Front	Review	Classification	Date	Reference	Figures	Attachments	Claims	KWC	Draw. De
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☐ 13. Document ID: US 5008211 A

L16: Entry 13 of 16

File: USPT

Apr 16, 1991

US-PAT-NO: 5008211

DOCUMENT-IDENTIFIER: US 5008211 A

TITLE: Method for forming FET with a super lattice channel

Full	Title	Citation	Front	Review	Classification	Date	Reference	Figures	Attachments	Claims	KWC	Draw. De
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☐ 14. Document ID: US 4945393 A

L16: Entry 14 of 16

File: USPT

Jul 31, 1990

US-PAT-NO: 4945393

DOCUMENT-IDENTIFIER: US 4945393 A

TITLE: Floating gate memory circuit and apparatus

Full	Title	Citation	Front	Review	Classification	Date	Reference	Figures	Attachments	Claims	KWC	Draw. De
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☐ 15. Document ID: US 4905063 A

L16: Entry 15 of 16

File: USPT

Feb 27, 1990

US-PAT-NO: 4905063

DOCUMENT-IDENTIFIER: US 4905063 A

TITLE: Floating gate memories

Full	Title	Citation	Front	Review	Classification	Date	Reference	Figures	Attachments	Claims	KWC	Draw. De
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☐ 16. Document ID: US 4799087 A

L16: Entry 16 of 16

File: USPT

Jan 17, 1989

US-PAT-NO: 4799087